

# 1N6373 - 1N6381 Series (ICTE-5 - ICTE-36)

## 1500 Watt Peak Power Mosorb™ Zener Transient Voltage Suppressors

### Unidirectional\*

Mosorb devices are designed to protect voltage sensitive components from high voltage, high-energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. These devices are ON Semiconductor's exclusive, cost-effective, highly reliable Surmetic™ axial leaded package and are ideally-suited for use in communication systems, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications, to protect CMOS, MOS and Bipolar integrated circuits.

#### Specification Features

- Working Peak Reverse Voltage Range - 5.0 V to 45 V
- Peak Power - 1500 Watts @ 1 ms
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage < 5  $\mu$ A Above 10 V
- Response Time is Typically < 1 ns
- Pb-Free Packages are Available\*

#### Mechanical Characteristics

**CASE:** Void-free, transfer-molded, thermosetting plastic

**FINISH:** All external surfaces are corrosion resistant and leads are readily solderable

**MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES:** 260°C, 1/16" from the case for 10 seconds

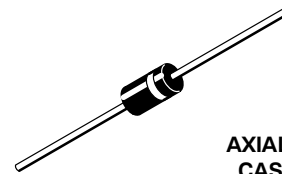
**POLARITY:** Cathode indicated by polarity band

**MOUNTING POSITION:** Any



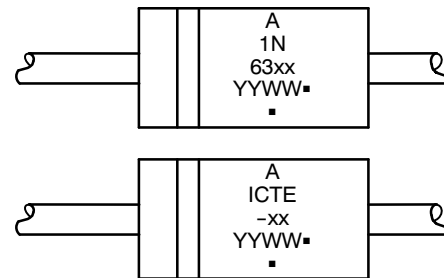
ON Semiconductor®

<http://onsemi.com>



AXIAL LEAD  
CASE 41A  
PLASTIC

#### MARKING DIAGRAMS



A = Assembly Location  
1N63xx = JEDEC Device Code  
ICTE-xx = ON Device Code  
YY = Year  
WW = Work Week  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
1N63xx, G	Axial Lead (Pb-Free)	500 Units/Box
1N63xxRL4, G	Axial Lead (Pb-Free)	1500/Tape & Reel
ICTE-xx, G	Axial Lead (Pb-Free)	500 Units/Box
ICTE-xxRL4, G	Axial Lead (Pb-Free)	1500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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## MAXIMUM RATINGS

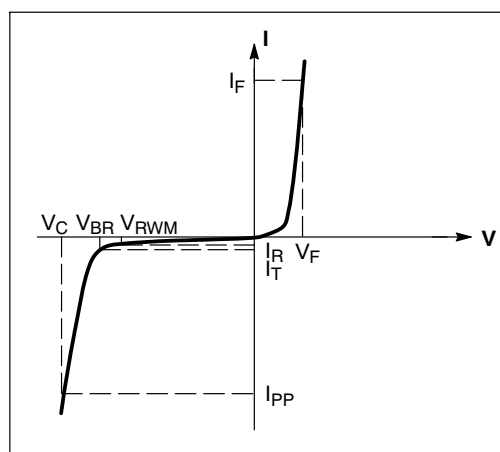
Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ $T_L \leq 25^\circ\text{C}$	$P_{PK}$	1500	W
Steady State Power Dissipation @ $T_L \leq 75^\circ\text{C}$ , Lead Length = 3/8" Derated above $T_L = 75^\circ\text{C}$	$P_D$	5.0 20	W mW/°C
Thermal Resistance, Junction-to-Lead	$R_{\theta JL}$	20	°C/W
Forward Surge Current (Note 2) @ $T_A = 25^\circ\text{C}$	$I_{FSM}$	200	A
Operating and Storage Temperature Range	$T_J, T_{stg}$	- 65 to +175	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Nonrepetitive current pulse per Figure 5 and derated above  $T_A = 25^\circ\text{C}$  per Figure 2.
2. 1/2 sine wave (or equivalent square wave),  $PW = 8.3$  ms, duty cycle = 4 pulses per minute maximum.

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 3.5$ V Max. @ $I_F$ (Note 3) = 100 A)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$\Theta V_{BR}$	Maximum Temperature Variation of $V_{BR}$
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$



## Uni-Directional TVS

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 3.5$ V Max. @ $I_F$ (Note 3) = 100 A)

JEDEC Device† (ON Device)	Device Marking	$V_{RWM}$ (Note 4) (Volts)	$I_R$ @ $V_{RWM}$ ( $\mu\text{A}$ )	Breakdown Voltage			$V_C$ @ $I_{PP}$ (Note 6)		$V_C$ (Volts) (Note 6)		$\Theta V_{BR}$ (mV/°C)	
				$V_{BR}$ (Note 5) (Volts)			$V_C$	$I_{PP}$	@ $I_{PP} = 1$ A	@ $I_{PP} = 10$ A		
				Min	Nom	Max						@ $I_T$
1N6373, G	1N6373	5.0	300	6.0	-	-	1.0	9.4	160	7.1	7.5	4.0
1N6374, G	1N6374	8.0	25	9.4	-	-	1.0	15	100	11.3	11.5	8.0
1N6375, G	1N6375	10	2.0	11.7	-	-	1.0	16.7	90	13.7	14.1	12
1N6376, G	1N6376	12	2.0	14.1	-	-	1.0	21.2	70	16.1	16.5	14
1N6377, G	1N6377	15	2.0	17.6	-	-	1.0	25	60	20.1	20.6	18
1N6380, G	1N6380	36	2.0	42.4	-	-	1.0	65.2	23	50.6	54.3	50
1N6381, G	1N6381	45	2.0	52.9	-	-	1.0	78.9	19	63.3	70	60
ICTE-5RLG	ICTE-5	5.0	300	6.0	-	-	1.0	9.4	160	7.1	7.5	4.0
ICTE-10RLG	ICTE-10	10	2.0	11.7	-	-	1.0	16.7	90	13.7	14.1	8.0
ICTE-12RLG	ICTE-12	12	2.0	14.1	-	-	1.0	21.2	70	16.1	16.5	12
ICTE-15RLG	ICTE-15	15	2.0	17.6	-	-	1.0	25	60	20.1	20.6	14
ICTE-18, G	ICTE-18	18	2.0	21.2	-	-	1.0	30	50	24.2	25.2	18
ICTE-36RLG	ICTE-36	36	2.0	42.4	-	-	1.0	65.2	23	50.6	54.3	26

3. Square waveform,  $PW = 8.3$  ms, non-repetitive duty cycle.
  4. A transient suppressor is normally selected according to the maximum working peak reverse voltage ( $V_{RWM}$ ), which should be equal to or greater than the dc or continuous peak operating voltage level.
  5.  $V_{BR}$  measured at pulse test current  $I_T$  at an ambient temperature of  $25^\circ\text{C}$  and minimum voltage in  $V_{BR}$  is to be controlled.
  6. Surge current waveform per Figure 5 and derate per Figures 1 and 2.
- †The "G" suffix indicates Pb-Free package or Pb-Free packages are available.

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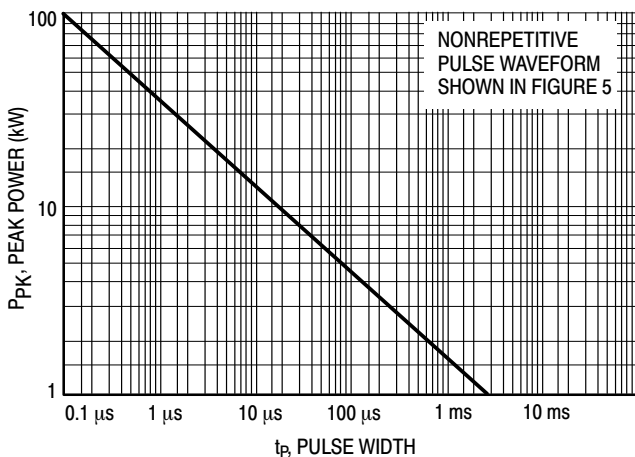


Figure 1. Pulse Rating Curve

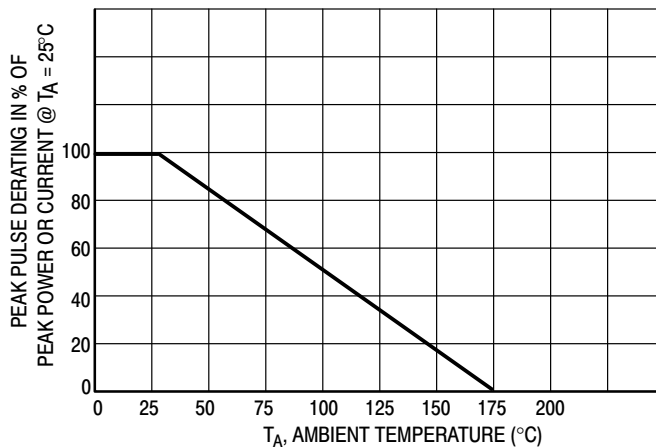


Figure 2. Pulse Derating Curve

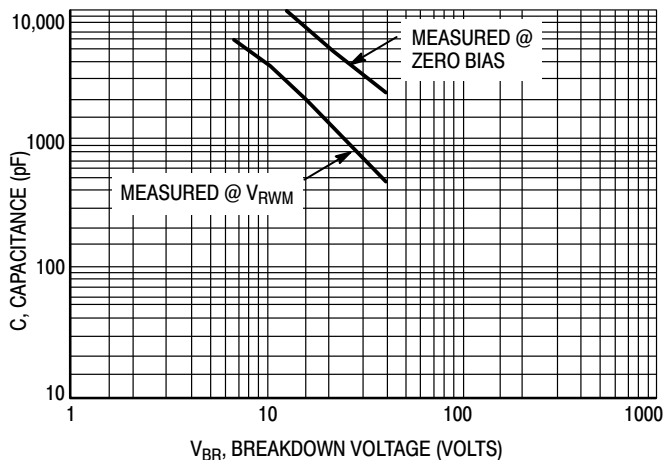


Figure 3. Capacitance versus Breakdown Voltage

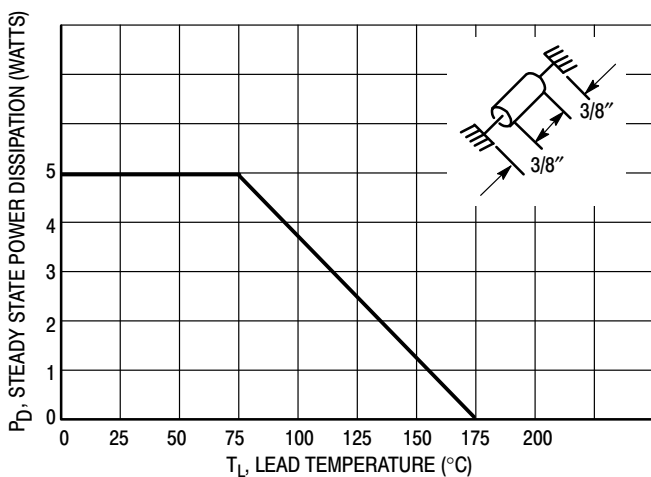


Figure 4. Steady State Power Derating

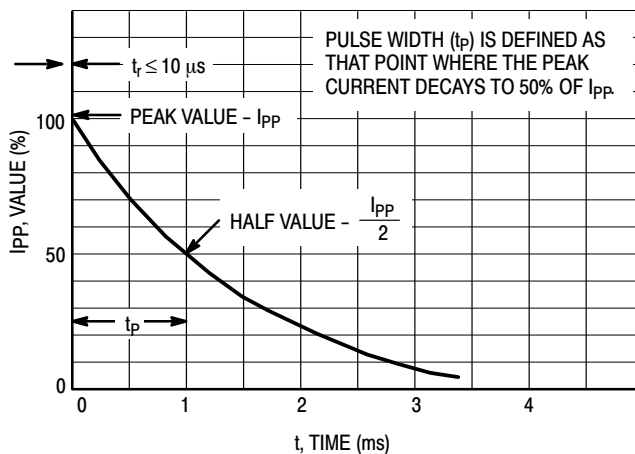


Figure 5. Pulse Waveform

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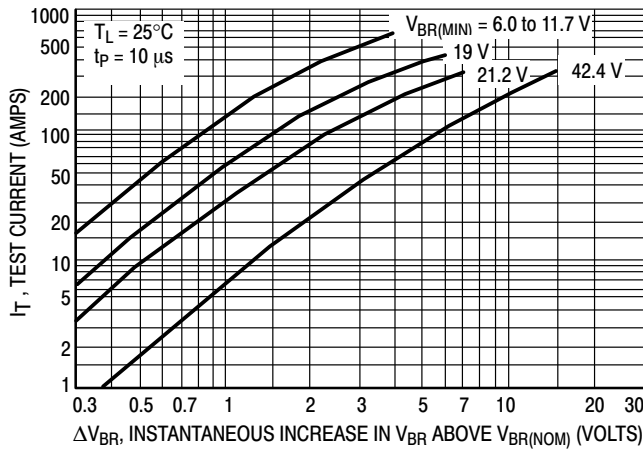


Figure 6. Dynamic Impedance

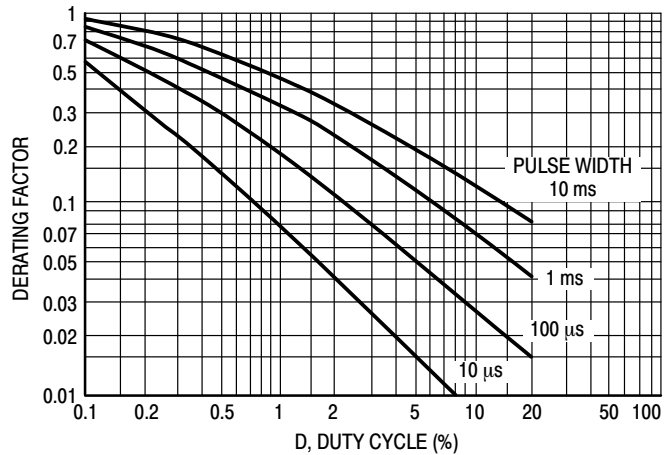


Figure 7. Typical Derating Factor for Duty Cycle

### APPLICATION NOTES

#### RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitance effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 8.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 9. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. These devices have excellent response time, typically in the picosecond range and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper

circuit layout, minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by  $Z_{in}$  is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

#### DUTY CYCLE DERATING

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 7. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 7 appear to be in error as the 10 ms pulse has a higher derating factor than the 10 μs pulse. However, when the derating factor for a given pulse of Figure 7 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.

TYPICAL PROTECTION CIRCUIT

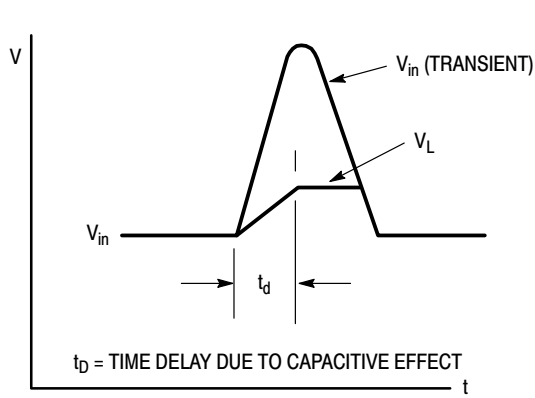
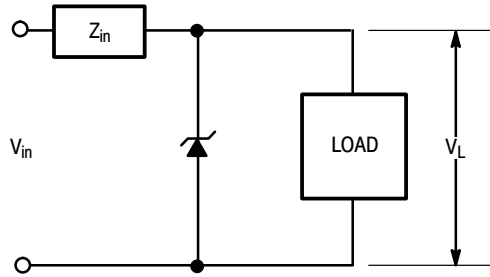


Figure 8.

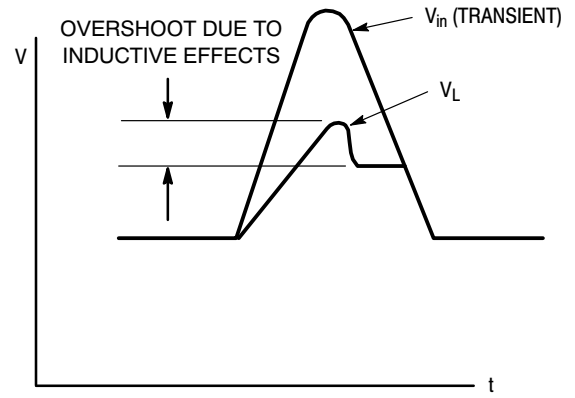
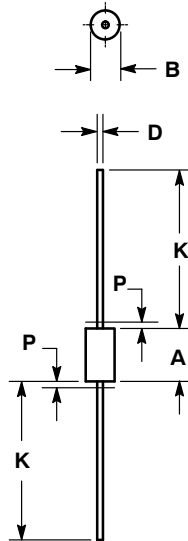


Figure 9.

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## PACKAGE DIMENSIONS

### MOSORB CASE 41A-04 ISSUE D




#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. LEAD FINISH AND DIAMETER UNCONTROLLED IN DIMENSION P.
4. 041A-01 THRU 041A-03 OBSOLETE, NEW STANDARD 041A-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.374	8.50	9.50
B	0.189	0.209	4.80	5.30
D	0.038	0.042	0.96	1.06
K	1.000	---	25.40	---
P	---	0.050	---	1.27

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